

FIG. 1A

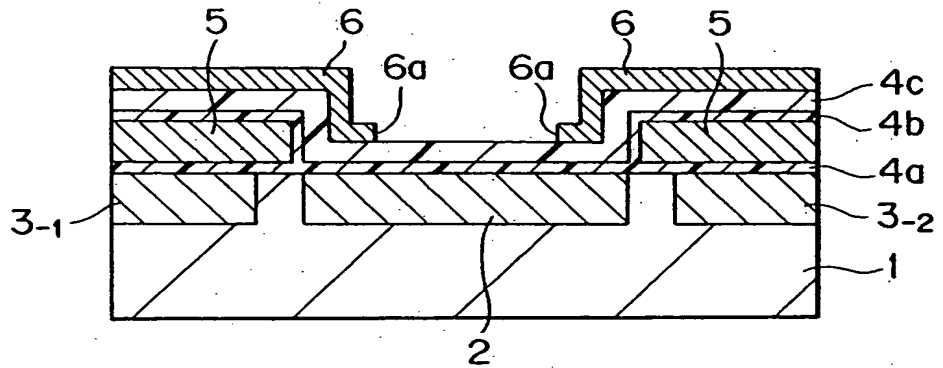


FIG. 1B

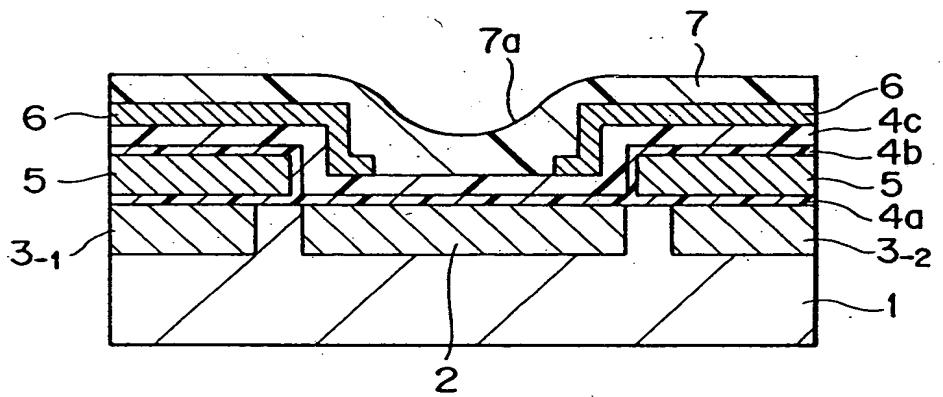


FIG. 1C

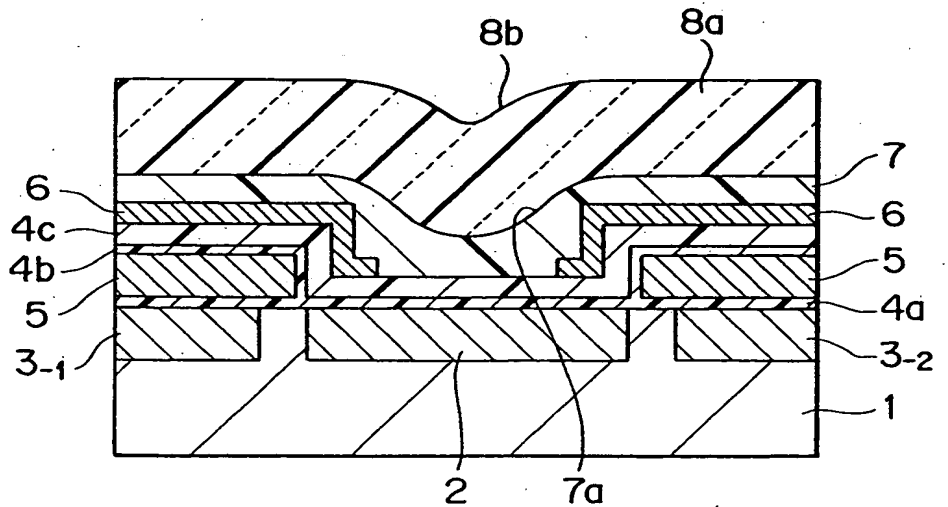


FIG. 2A

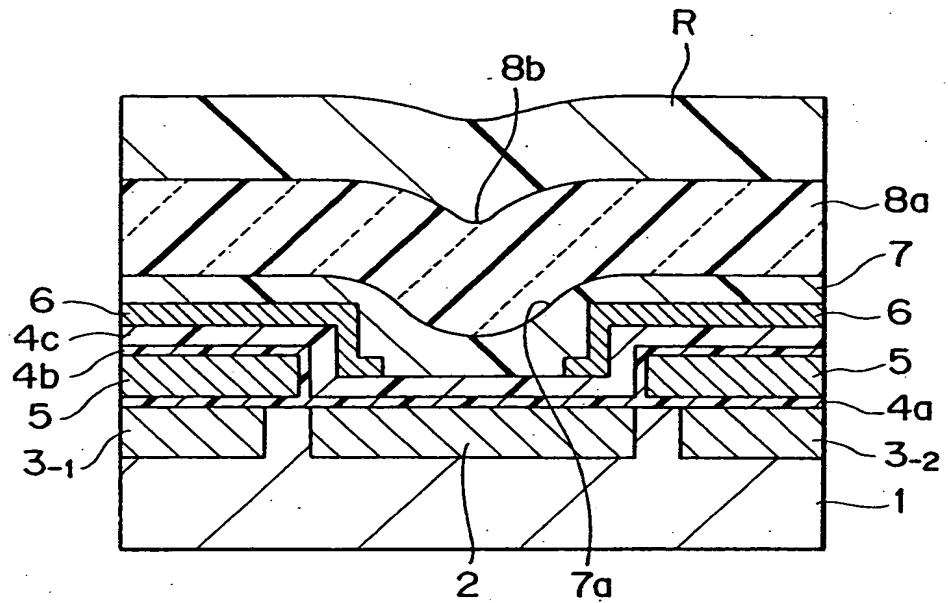


FIG. 2B

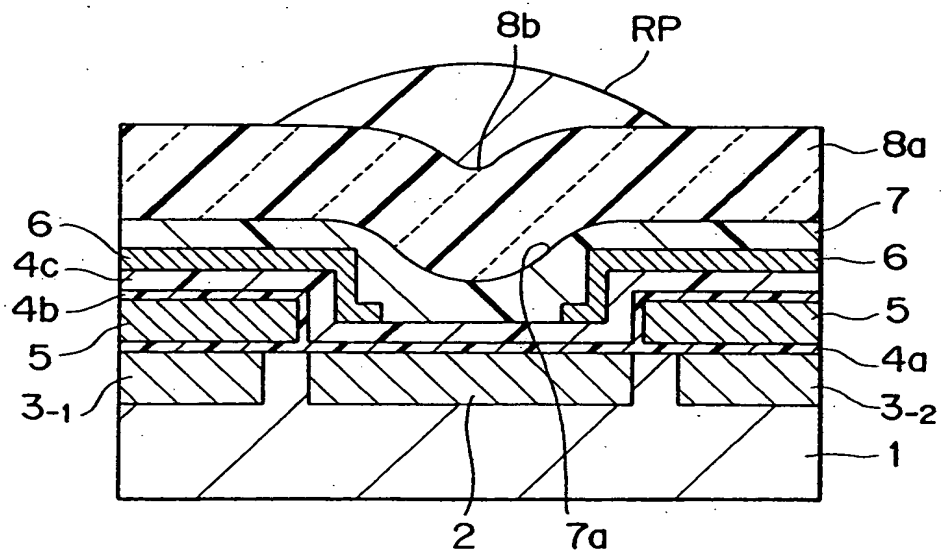


FIG. 4A-1

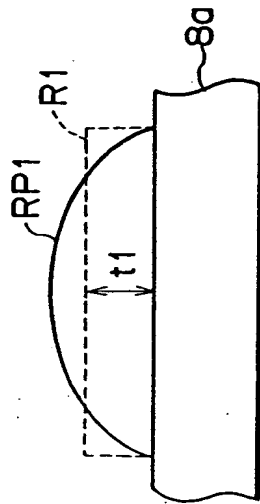


FIG. 4A-2

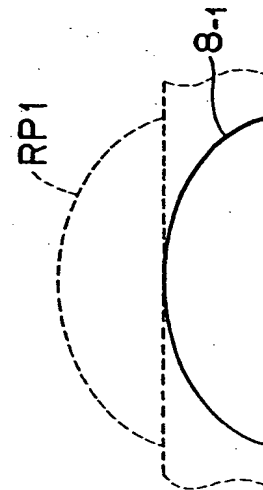


FIG. 4B-1

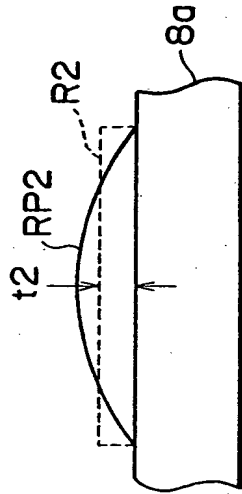


FIG. 4B-2

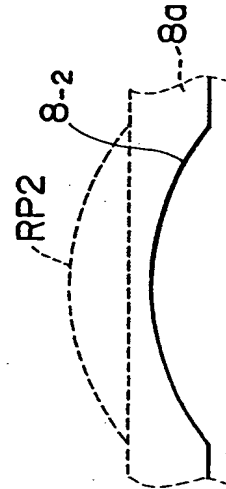


FIG. 4C-1

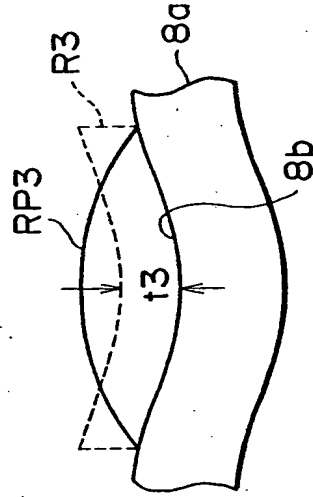


FIG. 4C-2

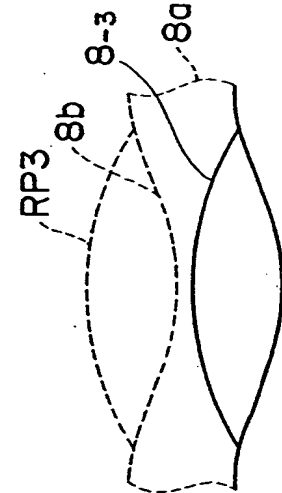


FIG. 5A

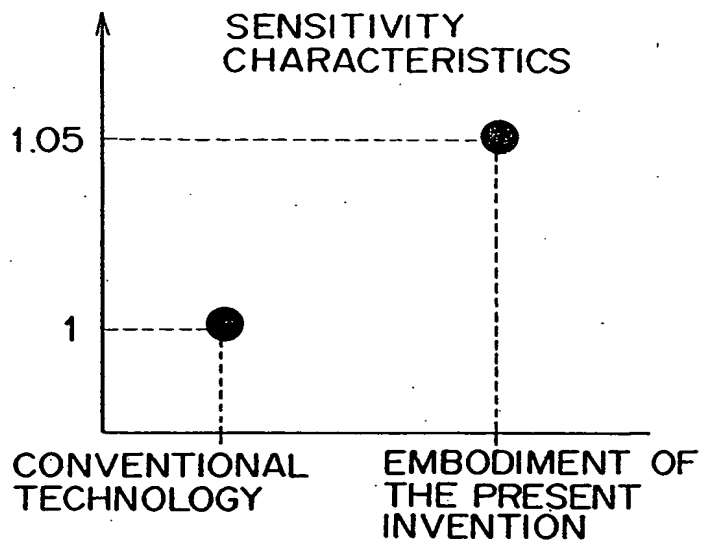


FIG. 5B

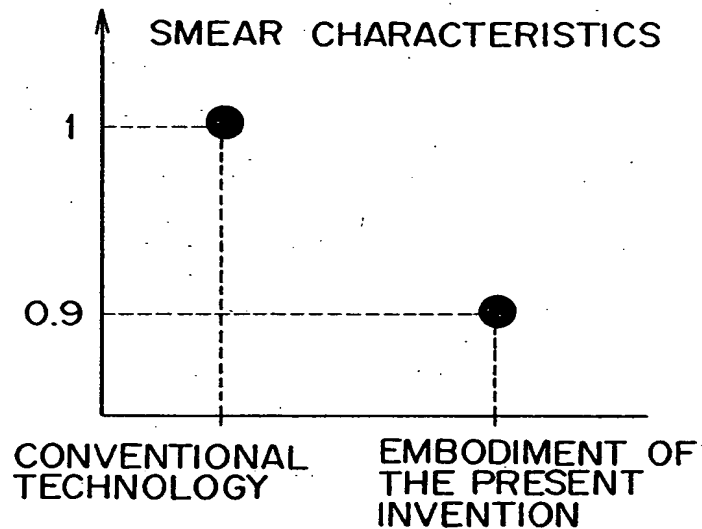
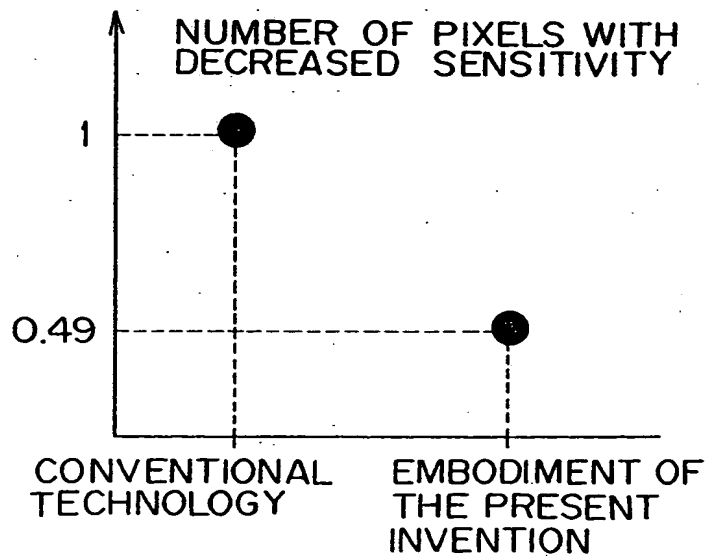


FIG. 5C



SOLID-STATE IMAGING DEVICE

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FIG. 6A

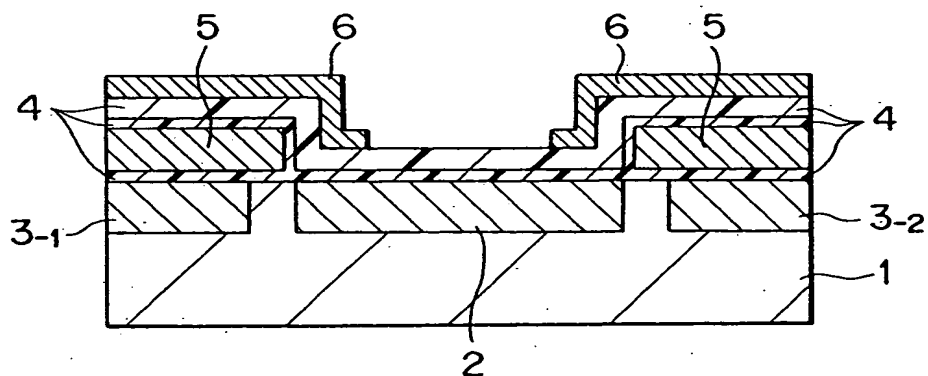


FIG. 6B

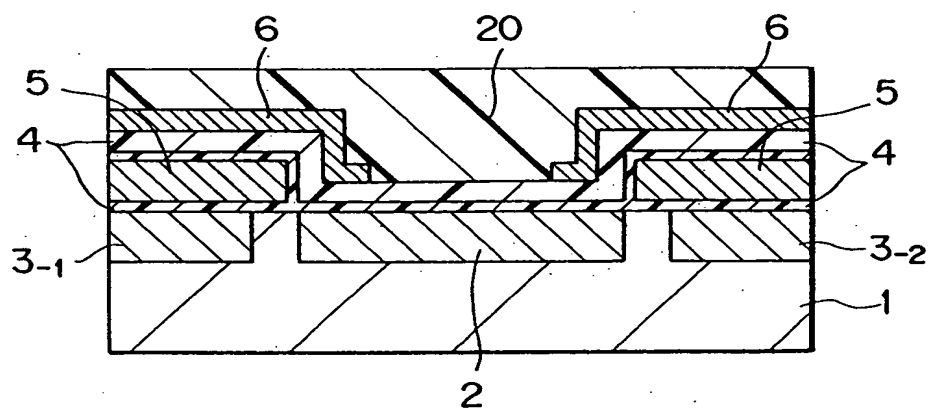
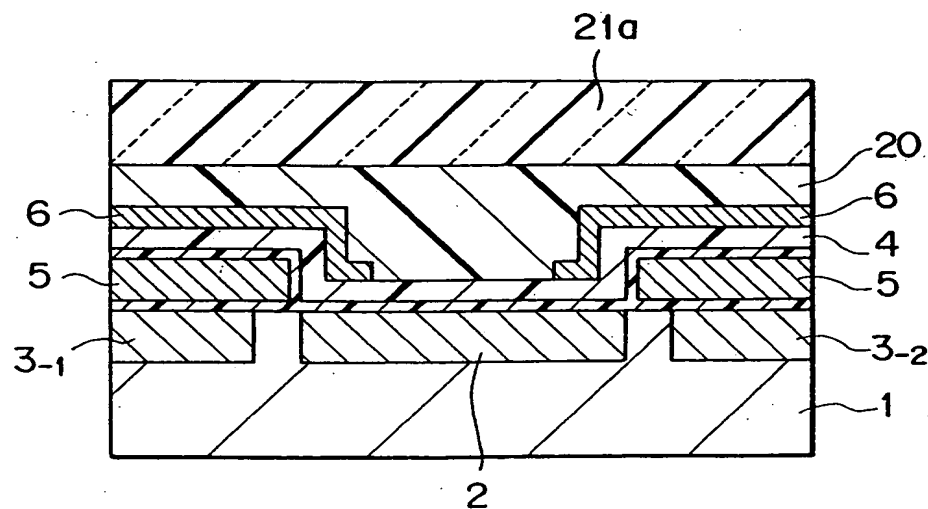


FIG. 6C



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[illegible]

FIG. 8A

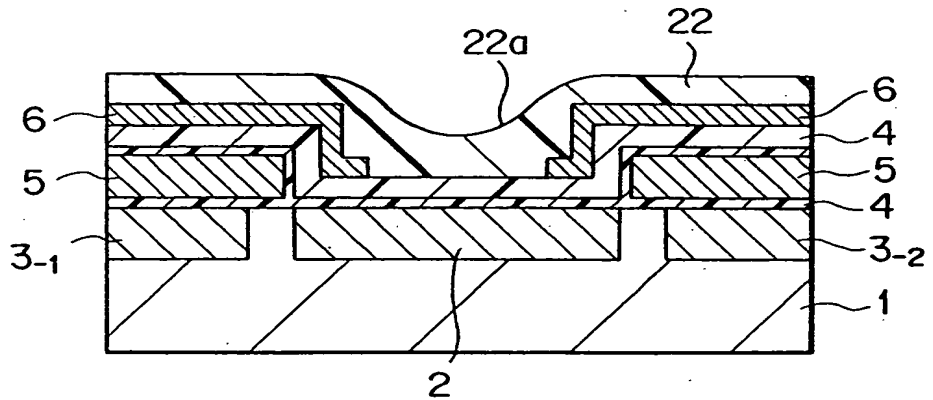


FIG. 8B

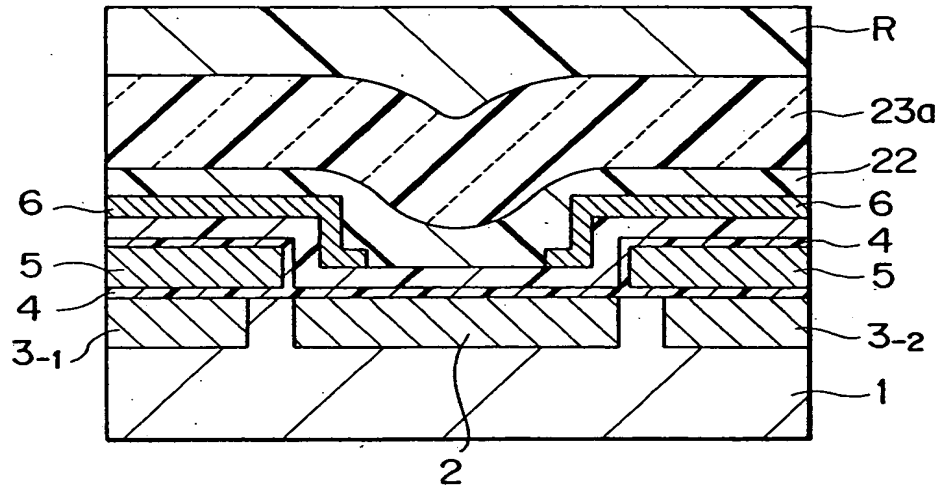


FIG. 8C

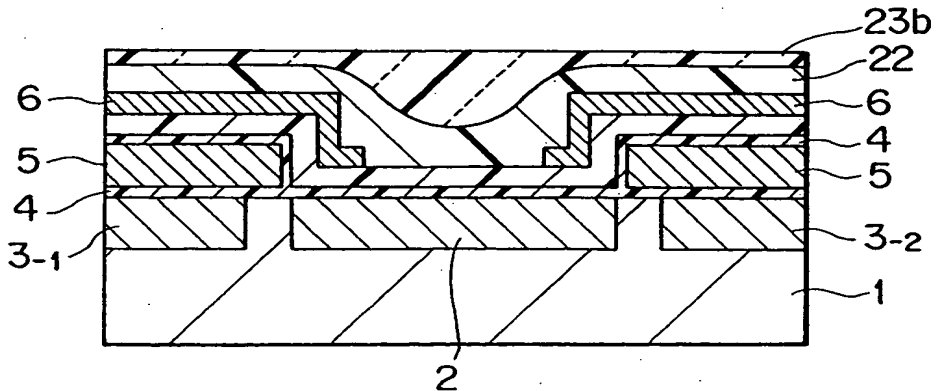


FIG. 9A

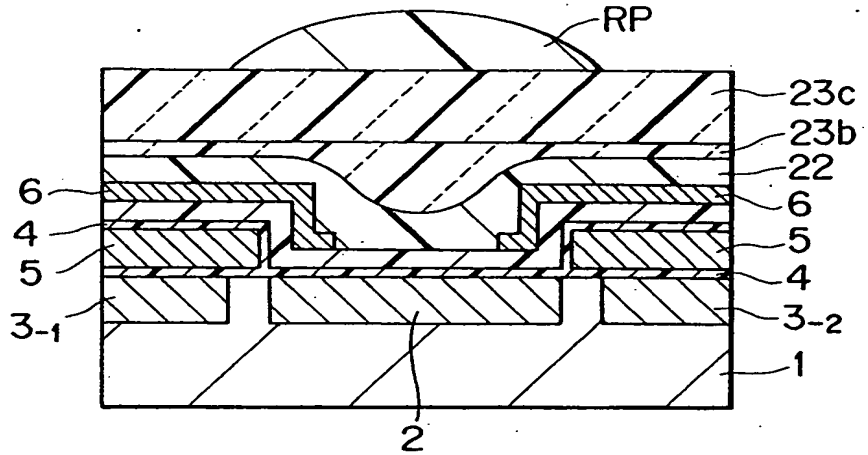


FIG. 9B

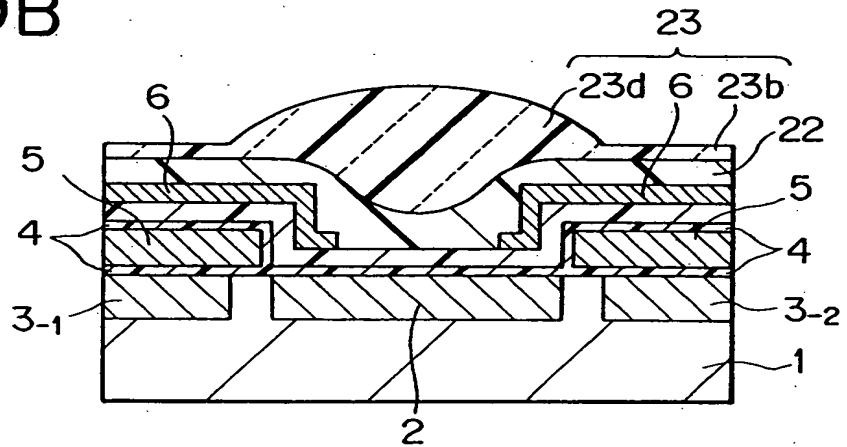
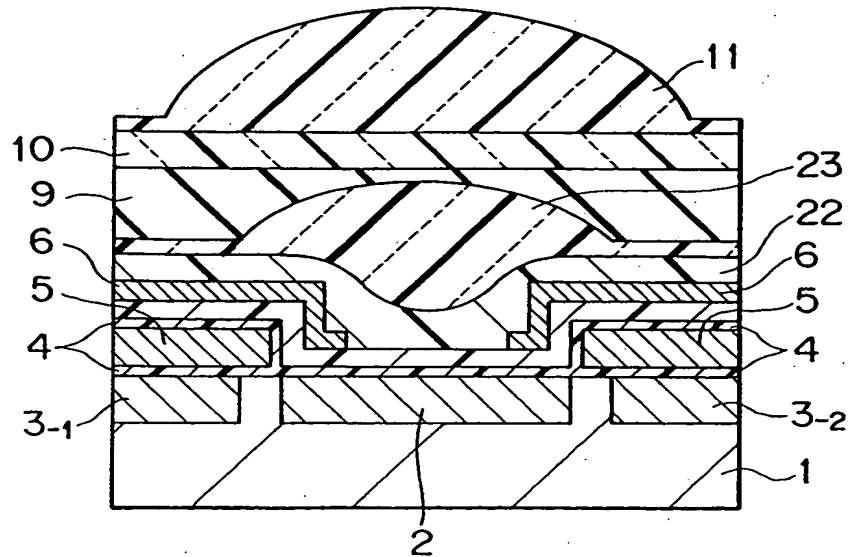


FIG. 9C



This diagram is a cross-sectional view of a semiconductor device. It features a substrate 1 with a series of rectangular openings 3-1 and 3-2. Above the substrate, there are several layers: a layer 5, a layer 4, another layer 5, a layer 6, and a layer 20. A central lens-like structure 11 is positioned above the substrate. Two dashed lines, labeled L0 and L1, represent optical paths that converge at a point within the lens structure 11. Other labels include 10, 21, 9, and 6, which point to specific layers or regions within the device structure.